

Measurement and Minimization of Wing Tilt in Laterally Overgrown GaN on a SiO₂ Mask

P. Fini, L. Zhao, J.S. Speck, S. P. DenBaars

Materials Department, University of California, Santa Barbara, CA 93106-5050 USA

Anneli Munkholm

Chemistry Division, Argonne National Laboratory, Argonne, IL 60439 USA

Carol Thompson, G.B. Stephenson, J.A. Eastman, M.V. Ramana Murty, O. Auciello

*Materials Science Division, Argonne National Laboratory, Argonne, IL 60439*Materials Science Division
Argonne National Laboratory
Argonne, IL 60439RECEIVED
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8. Authors

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